



EpiX[®] C2C: automated wafer mapping

Combining white light reflectance and photoluminescence, the EpiX[®] C2C system ensures a comprehensive 2D analysis of critical wafer properties by non-contact optical measurements. The cassette-to-cassette configuration of EpiX[®] C2C allows to achieve the high throughput required in industrial applications.

Features

- Automated white light reflectance (WLR) and photoluminescence (PL) wafer mapping
- Post-process quality control of entire wafer area with EpiX[®]
- Extended spectral range 250–2400 nm
- Spectral resolution down to 0.1 nm
- XY mapping stage with automated wafer thickness compensation
- Up to 4 configurable laser wavelengths
- Adjustable laser power
- Predefined and customized algorithms
- Up to two load ports for 3", 100 mm, 150 mm & 200 mm cassettes
- Prealigner (optional)
- Wafer-ID Reader (optional)
- Fan-Filter-Units (optional)

Benefits

- Industry-compatible clean room design (up to ISO 3)
- High throughput
- Automated normalization of measurement data
- Wide set of standard analysis methods
- Automated yield analysis
- Combination of complementary in-situ and ex-situ metrology for in-depth and areal wafer analysis through **Connected Metrology[®]**

Parameters Mapping Stage	
XY scan area	≤ 200 mm diameter
Normalization (WLR & PL)	Automatic using reference sample
Sample holder	Continuous vacuum chuck
Wafer thickness compensation	Distance sensor & z-stage (optional)
Mapping speed 100 mm wafer @ 1.0 mm pitch	200 s
Mapping speed 150 mm wafer @ 2.0 mm pitch	150 s

Spectroscopic Reflectance Measurements	
Optical head	Combined optical head for WLR and PL measurements
Spot size	configurable: 100 μm, 200 μm, 300 μm
WLR light source	Tungsten lamp 2915 K (alternative UV light source available)
Spectral range	configurable: 230 nm to 2400 nm
Spectral resolution	≥ 0.1 nm, depending on grating
Number of gratings	Up to 4
Alternative spectrometer configuration	Multiple fixed spectrometers measure in parallel
Absolute accuracy at wafer center	< ± 0.5 %
Signal to noise within single spectrum	< ± 0.5 %
System-induced deviation across wafer	< ± 0.5 %

Photoluminescence Measurements	
Up to 4 laser sources configurable	Default: 405 nm, 532 nm, 785 nm, other wavelengths upon request
Laser power on sample for default setup	405 nm: > 25 mW 532 nm, 785 nm: > 80 mW
Intensity stability across wafer	< ± 3 %
Signal to noise within single spectrum	< ± 1 %

Analysis Features

Software modifiers

- Edge exclusion
- Virtual rotation

Algorithms

- Predefined and customized
- VCSEL analysis
- Single film thickness/composition
- Multi peak analysis (analytic/numeric)
- Wafer thickness
- Full spectral fitting (+connected metrology option)

Virtual die patterns

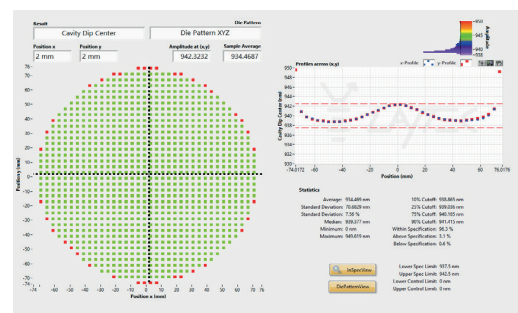
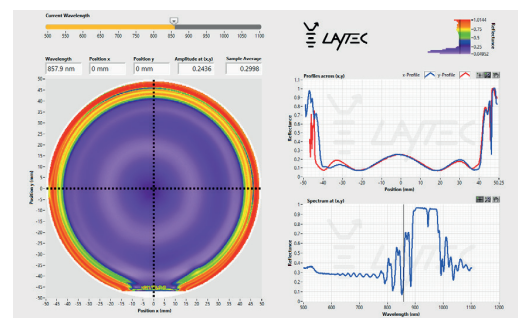
- Die pattern assignment
- Import of customer die layout

Automated yield analysis

- Wafer level
- Die level

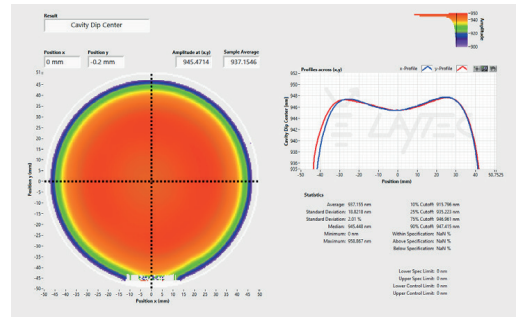
Reports

- XML reports, PDF reports, ASCII exports



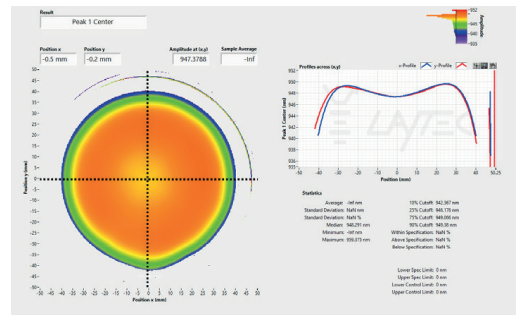
White light reflectance and VCSEL analysis

- Stop band: center, width, edges, height
- FP-Dip: center, width, height, area
- Identical to in-situ analysis in EpiNet for EpiTT VCSEL

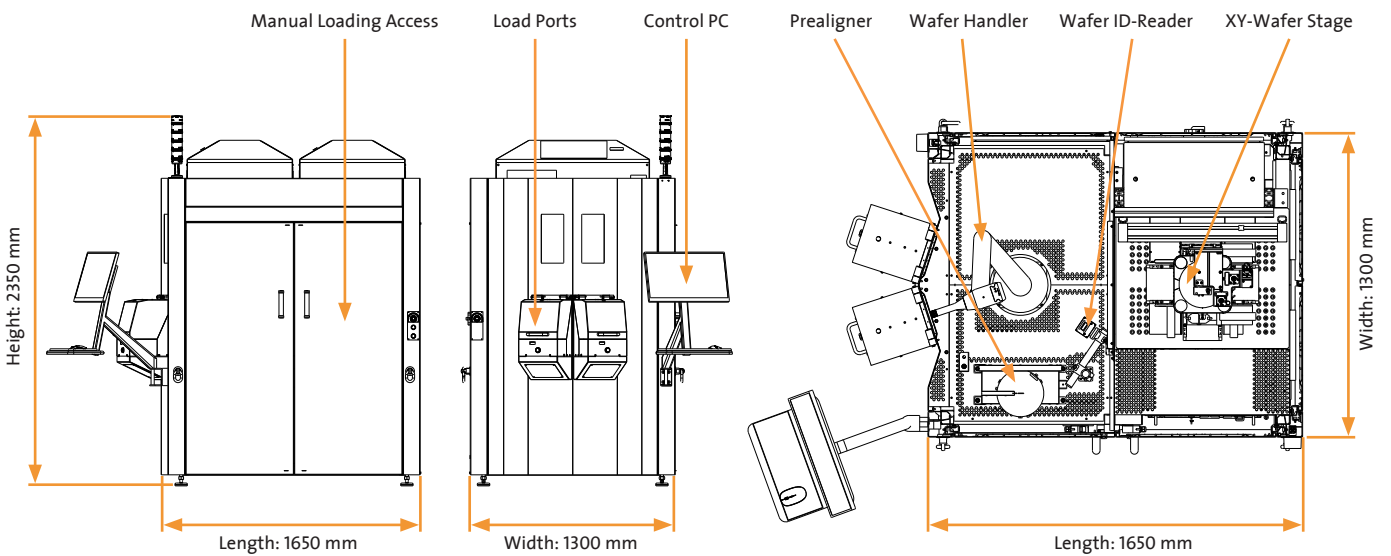


Photoluminescence & multi peak analysis

- Peak types: Gauss, Lorentz, numeric analysis
- Output results: peak wavelength, center wavelength, centroid wavelength, dominant wavelength, height, width, area, asymmetry



EpiX® C2C Layout

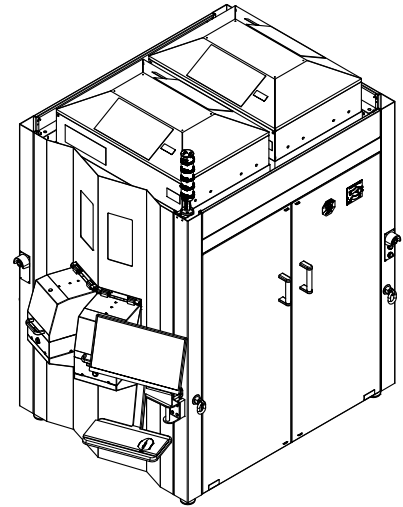


Options

Parameter	Basic	Options
Load ports	1	Up to 2
Cassette type	Open cassette	Open cassette, SMIF, FOUP
Wafer size	3", 100 mm, 150 mm & 200 mm	3", 100 mm, 150 mm & 200 mm (other sizes upon request)
Prealigner	Software alignment	Optional
Wafer ID reader		Optional, from above and below
Fan-Filter-Unit		Optional

Dimensions & Connections

Footprint (WxDxH)	~ 1300 x 1650 (+300) x 2500 mm
Mass	~ 1400 kg
Power supply	230 V / 16 A CEE 7/4 (CE version) 208 V / 20 A (international / UL version)
Vacuum	8 mm, if present, else internal vacuum option available
Network	RJ45
Operating conditions	Clean room or comparable laboratory, temperature 22 ± 2 °C, humidity < 55 %
Laser classification	CLASS 1 LASER PRODUCT according to DIN-EN60825-1:2015-07



EpiX® C2C is designed with multiple upgrade options: extended wavelength range, software interfaces (e.g. for user-owned spectral analysis libraries) upon request.



Specifications are subject to further technical development and may differ from those given in the data sheet. Please consult our technical sales team to see how LayTec metrology can best serve your specific application.

For further information please contact:

LayTec AG
Seesener Str. 10-13
10709 Berlin, Germany

Tel.: +49 (0)30 89 00 55-0
Fax: +49 (0)30 89 00 55-180
Email: info@laytec.de
Web: laytec.de



MEMBER OF THE NYNOMIC GROUP

Developed,
manufactured and
qualified in Germany.

Version 11 • 2024